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(54) Title: METHOD AND APPARATUS FOR CLEANING SEMICONDUCTOR WAFER

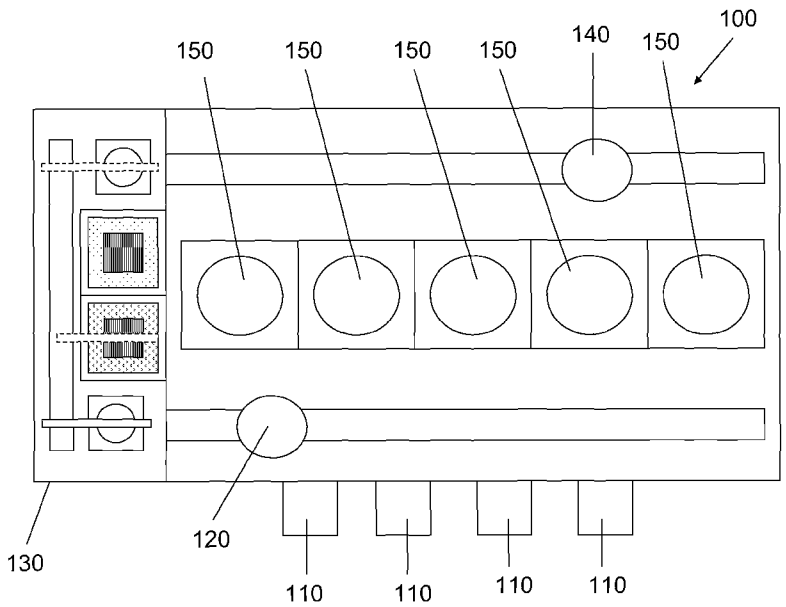


FIG. 1

(57) Abstract: A method and apparatus(100) for cleaning semiconductor wafer are provided, combining batch cleaning and single wafer cleaning together. The method includes the following steps: tacking at least two wafers from a cassette in a load port(110) and putting said wafers into a first tank(137) filled with chemical solution; after said wafers have been processed in the first tank(137), taking said wafers out of the first tank(137) and keeping said wafers in wet status; putting said wafers into a second tank(138) filled with liquid; after said wafers have been processed in the second tank(138), taking said wafers out of the second tank(138) and keeping said wafers in wet status; putting one of said wafers on a chuck inside a single wafer cleaning module(150); rotating the chuck while applying chemical solution on said wafer; applying deionized water on said wafer; drying said wafer; taking said wafer out of the single wafer cleaning module(150) and then putting said wafer back to the cassette in the load port(110).

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